

COMPLEMENTARY SILICON POWER TRANSISTORS

...designed for use in general-purpose amplifier and switching applications

FEATURES:

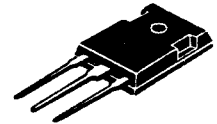
- * Power Dissipation - $P_D = 90W @ T_C = 25^\circ C$
- * DC Current Gain $hFE = 20 \sim 100 @ I_C = 4.0 A$
- * $V_{CE(sat)} = 1.1 V (Max.) @ I_C = 4.0 A, I_B = 400 mA$

NPN **PNP**
TIP3055 **TIP2955**

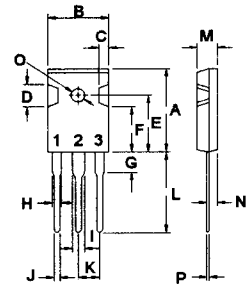
15 AMPERE
COMPLEMENTARY SILICON
POWER TRANSISTORS
60 VOLTS
90 WATTS

MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	60	V
Collector-Emitter Voltage	V_{CER}	70	V
Collector-Base Voltage	V_{CBO}	100	V
Emitter-Base Voltage	V_{EBO}	7.0	V
Collector Current-Continuous	I_C	15	A
Base Current	I_B	7.0	A
Total Power Dissipation @ $T_C = 25^\circ C$ Derate above $25^\circ C$	P_D	90 0.72	W W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +150	$^\circ C$



TO-247(3P)



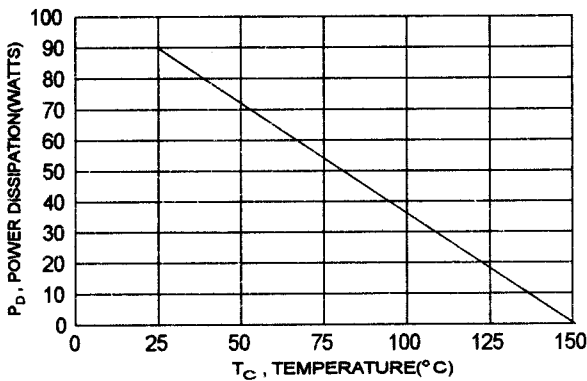
PIN 1.BASE
2.COLLECTOR
3.EMITTER

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.39	$^\circ C/W$

DIM	MILLIMETERS	
	MIN	MAX
A	20.63	22.38
B	15.38	16.20
C	1.90	2.70
D	5.10	6.10
E	14.81	15.22
F	11.72	12.84
G	4.20	4.50
H	1.82	2.46
I	2.92	3.23
J	0.89	1.53
K	5.26	5.66
L	18.50	21.50
M	4.68	5.36
N	2.40	2.80
O	3.25	3.65
P	0.55	0.70

FIGURE -1 POWER DERATING



ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Sustaining Voltage (1) ($I_C = 30\text{ mA}$, $I_B = 0$)	$V_{CE(sus)}$	60		V
Collector Cutoff Current ($V_{CE} = 70\text{ V}$, $R_{BE} = 100\text{ ohm}$)	I_{CER}		1.0	mA
Collector Cutoff Current ($V_{CE} = 30\text{ V}$, $I_B = 0$)	I_{CEO}		0.7	mA
Collector Cutoff Current ($V_{CE} = 100\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$)	I_{CEV}		5.0	mA
Emitter Cutoff Current ($V_{EB} = 7.0\text{ V}$, $I_C = 0$)	I_{EBO}		5.0	mA

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 4.0\text{ A}$, $V_{CE} = 4.0\text{ V}$) ($I_C = 10\text{ A}$, $V_{CE} = 4.0\text{ V}$)	h_{FE}	20 5.0	100	
Collector - Emitter Saturation Voltage ($I_C = 4.0\text{ A}$, $I_B = 0.4\text{ A}$) ($I_C = 10\text{ A}$, $I_B = 3.3\text{ A}$)	$V_{CE(sat)}$		1.1 3.0	V
Base - Emitter On Voltage ($I_C = 4.0\text{ A}$, $V_{CE} = 4.0\text{ V}$)	$V_{BE(on)}$		1.8	V

DYNAMIC CHARACTERISTICS

Current Gain - Bandwidth Product ($I_C = 500\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 1.0\text{ MHz}$)	f_T	2.5		MHz
Small-Signal Current Gain ($I_C = 1.0\text{ A}$, $V_{CE} = 4.0\text{ V}$, $f = 1\text{ KHz}$)	h_{FE}	15		

(1) Pulse Test: Pulse width = $300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$ (2) $f_T = |h_{fe}| \cdot f_{test}$

FIG-2 DC CURRENT GAIN

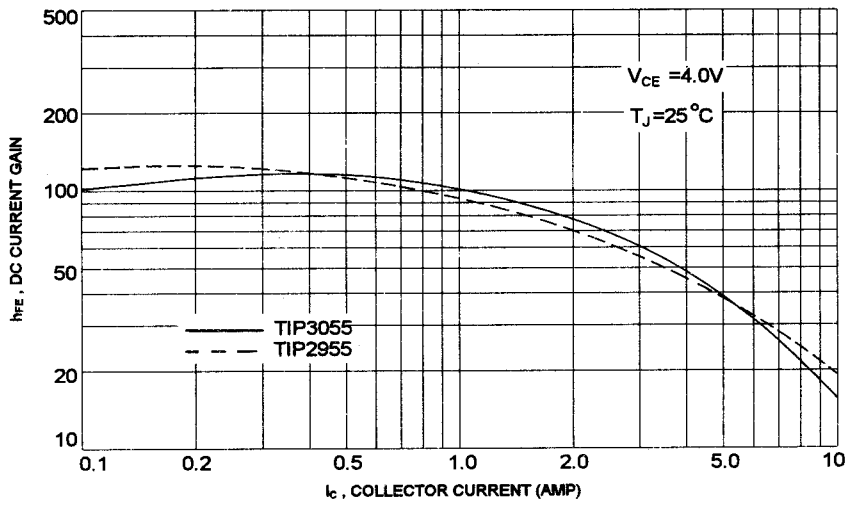
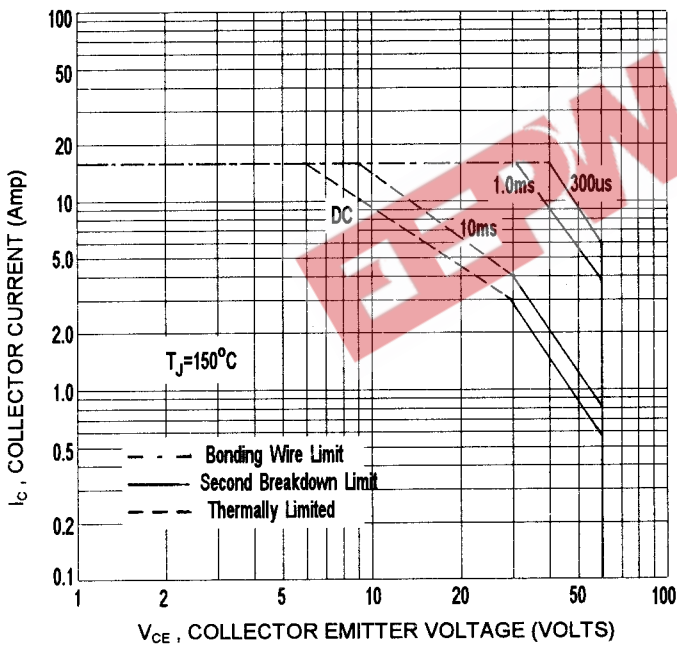


FIG-3 ACTIVE-REGION SAFE OPERATING AREA



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of FIG-3 is base on $T_C = 150^\circ C$; $T_{J(PK)}$ is variable depending on power level. second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature.